BLF189XRB; BLF189XRBS

Power LDMOS transistor

AMPLEON

Rev. 1 — 3 October 2017

Product data sheet

1. Product profile

1.1 General description

A 1900 W extremely rugged LDMOS power transistor for industrial pulsed applications in the HF to 150 MHz band.

Table 1. Application information

Test signal	f	V _{DS}	PL	G _p	ησ
	(MHz)	(V)	(W)	(dB)	(%)
pulsed RF	108	50	1900	26	72.5

1.2 Features and benefits

- Easy power control
- Integrated dual sided ESD protection enables class C operation and complete switch off of the transistor
- Excellent ruggedness VSWR > 65 : 1
- High efficiency
- Excellent thermal stability
- Compliant to Directive 2002/95/EC, regarding Restriction of Hazardous Substances (RoHS)

1.3 Applications

Industrial, scientific and medical applications

Pinning information 2.

Table 2. **Pinning**

Pin	Description		Simplified outline	Graphic symbol
BLF189XR	RB (SOT539A)			
1	drain1			
2	drain2		1 2	
3	gate1		5	3
4	gate2		3 4	5
5	source	[1]		4
				' <u></u>
				2 sym117
BLF189XR	RBS (SOT539B)			
1	drain1			
2	drain2		1 2	1
3	gate1		5	
4	gate2		3 4	3 — 5
5	source	[1]		4
				'
				2 sym117
				<u> </u>

^[1] Connected to flange.

Ordering information 3.

Table 3. **Ordering information**

Type number	Packag	ackage					
	Name	Description	Version				
BLF189XRB	-	flanged balanced ceramic package; 2 mounting holes; 4 leads	SOT539A				
BLF189XRBS	-	earless flanged balanced ceramic package; 4 leads	SOT539B				

Limiting values

Table 4. **Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage		-	135	V
V_{GS}	gate-source voltage		-6	+11	V
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature	[1]	-	225	°C

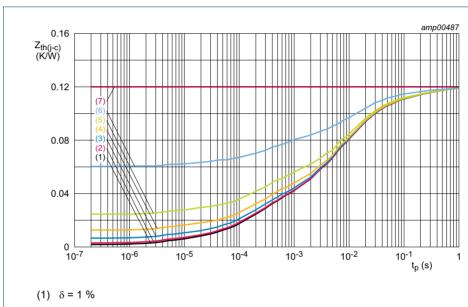
^[1] Continuous use at maximum temperature will affect the reliability, for details refer to the online MTF calculator.

5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions		Тур	Unit
R _{th(j-c)}	thermal resistance from junction to case	T _j = 150 °C	[1][2]	0.12	K/W
$Z_{\text{th(j-c)}}$	transient thermal impedance from junction to case	T_j = 150 °C; t_p = 100 μs; δ = 20 %		0.036	K/W

- [1] T_i is the junction temperature.
- [2] $R_{th(j-c)}$ is measured under RF conditions.
- [3] See Figure 1.



- (2) $\delta = 2 \%$
- (3) $\delta = 5 \%$
- (4) $\delta = 10 \%$
- (5) $\delta = 20 \%$
- (6) $\delta = 50 \%$
- (7) $\delta = 100 \% (DC)$

Fig 1. Transient thermal impedance from junction to case as a function of pulse duration

6. Characteristics

Table 6. DC characteristics

 $T_j = 25$ °C; per section unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{(BR)DSS}$	drain-source breakdown voltage	$V_{GS} = 0 \text{ V}; I_D = 7.8 \text{ mA}$	135	-	-	V
V _{GS(th)}	gate-source threshold voltage	$V_{DS} = 10 \text{ V}; I_D = 780 \text{ mA}$	1.33	1.9	2.33	V
V_{GSq}	gate-source quiescent voltage	$V_{DS} = 50 \text{ V}; I_{D} = 100 \text{ mA}$	1.10	1.67	2.10	V
I _{DSS}	drain leakage current	V _{GS} = 0 V; V _{DS} = 50 V	-	-	2.8	μΑ

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Table 6. DC characteristics ...continued

 $T_i = 25$ °C; per section unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{DSX}	drain cut-off current	$V_{GS} = V_{GS(th)} + 3.75 \text{ V};$ $V_{DS} = 10 \text{ V}$	-	106	-	Α
I _{GSS}	gate leakage current	$V_{GS} = 11 \text{ V}; V_{DS} = 0 \text{ V}$	-	-	280	nA
R _{DS(on)}	drain-source on-state resistance	$V_{GS} = V_{GS(th)} + 3.75 \text{ V};$ $I_D = 27.3 \text{ A}$	-	0.06	-	Ω

Table 7. AC characteristics

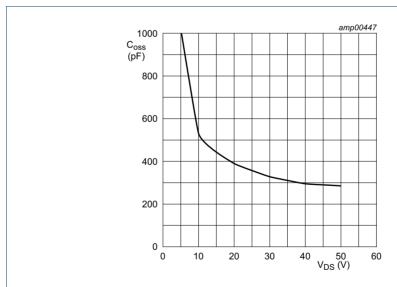
 $T_i = 25$ °C; per section unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
C _{rs}	feedback capacitance	$V_{GS} = 0 \text{ V}; V_{DS} = 50 \text{ V}; f = 1 \text{ MHz}$	-	6.7	-	pF
C _{iss}	input capacitance	$V_{GS} = 0 \text{ V}; V_{DS} = 50 \text{ V}; f = 1 \text{ MHz}$	-	750	-	pF
Coss	output capacitance	$V_{GS} = 0 \text{ V}; V_{DS} = 50 \text{ V}; f = 1 \text{ MHz}$	-	284	-	pF

Table 8. RF characteristics

Test signal: pulsed RF; t_p = 100 μ s; δ = 20 %; f = 108 MHz; RF performance at V_{DS} = 50 V; I_{Dq} = 200 mA; T_{case} = 25 °C; unless otherwise specified; in a class-AB production test circuit.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Gp	power gain	P _L = 1900 W	24.5	26	-	dB
RLin	input return loss	P _L = 1900 W	-	-9	-	dB
η_{D}	drain efficiency	P _L = 1900 W	69	72.5	-	%



 $V_{GS} = 0 V$; f = 1 MHz.

Fig 2. Output capacitance as a function of drain-source voltage; typical values per section

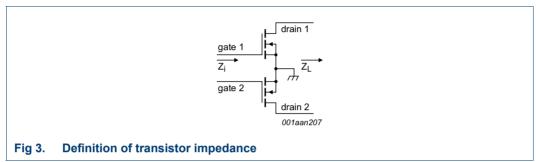
7. Test information

7.1 Ruggedness in class-AB operation

The BLF189XRB and BLF189XRBS are capable of withstanding a load mismatch corresponding to VSWR > 65 : 1 through all phases under the following conditions: $V_{DS} = 50 \text{ V}$; $I_{Dq} = 200 \text{ mA}$; $P_L = 1900 \text{ W}$ pulsed; f = 108 MHz.

7.2 Impedance information

Table 9.

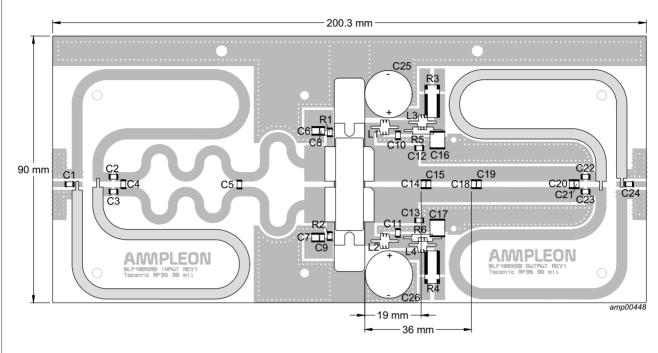


Typical push-pull impedance

Simulated Z_i and Z_L device impedance; impedance info at $V_{DS} = 50 \text{ V}$ and $P_L = 1900 \text{ W}$.

f	Z _i	Z _L
(MHz)	(Ω)	(Ω)
108	1.7 – j6.0	2.0 + j0.4

7.3 Test circuit



Printed-Circuit Board (PCB): RF-35; ϵ_r = 3.5 F/m; thickness = 0.765 mm; thickness copper plating = 35 μ m. See Table 10 for a list of components.

Fig 4. Component layout for class-AB production test circuit

Table 10. List of components For test circuit see Figure 4.

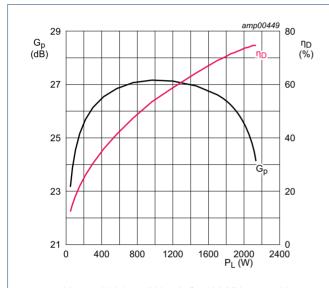
Component	Description	Value	Remarks
C1	multilayer ceramic chip capacitor	470 pF [1	
C2, C3	multilayer ceramic chip capacitor	68 pF	
C4	multilayer ceramic chip capacitor	43 pF	
C5	multilayer ceramic chip capacitor	240 pF	
C6, C7	multilayer ceramic chip capacitor	4.7 μF, 50 V	
C8, C9	multilayer ceramic chip capacitor	920 pF [1	1
C10, C11	multilayer ceramic chip capacitor	920 pF [1	1
C12, C13	multilayer ceramic chip capacitor	160 pF	1
C14, C15	multilayer ceramic chip capacitor	120 pF	1
C16, C17	multilayer ceramic chip capacitor	4.7 μF, 100 V	
C18, C19	multilayer ceramic chip capacitor	51 pF [1	1
C20, C21	multilayer ceramic chip capacitor	56 pF [1	1
C22, C23	multilayer ceramic chip capacitor	100 pF	1
C24	multilayer ceramic chip capacitor	470 pF	1
C25, C26	electrolytic capacitor	2200 μF, 64 V	
L1, L2	air inductor	3 turns, D = 4 mm	1mm copper wire
L3, L4	air inductor	5 turns, D = 4 mm	1mm copper wire

Table 10. List of components ...continued For test circuit see Figure 4.

Component	Description	Value	Remarks
R1, R2	resistor	4.7 kΩ	SMD 1206
R3, R4	resistor	0.01 Ω	FC4L110R010FER
R5, R6	resistor	4.7 Ω, 0.6 w	SMD 1206
T1, T2	semi rigid coax	50 Ω, 160 mm	EZ 141-AL-TP/M17

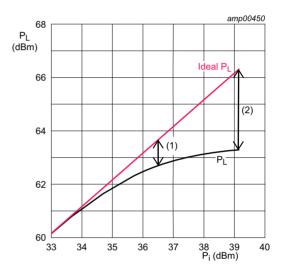
^[1] American Technical Ceramics type 100B or capacitor of same quality

7.4 Graphical data



 V_{DS} = 50 V; I_{Dq} = 200 mA; f = 108 MHz; t_p = 100 $\mu s;$ δ = 20 %.

Fig 5. Power gain and drain efficiency as function of output power; typical values



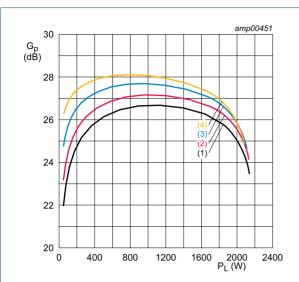
 V_{DS} = 50 V; I_{Dq} = 200 mA; f = 108 MHz; t_p = 100 $\mu s;$ δ = 20 %.

- (1) $P_{L(1dB)} = 62.7 \text{ dBm } (1870 \text{ W})$
- (2) $P_{L(3dB)} = 63.3 \text{ dBm } (2132 \text{ W})$

Fig 6. Output power as a function of input power; typical values

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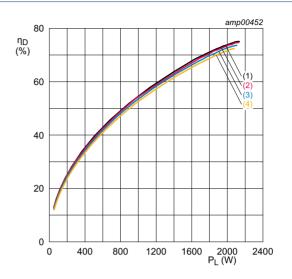
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 V_{DS} = 50 V; f = 108 MHz; t_p = 100 μ s; δ = 20 %.

- (1) $I_{Dq} = 50 \text{ mA}$
- (2) $I_{Dq} = 200 \text{ mA}$
- (3) $I_{Dq} = 800 \text{ mA}$
- (4) $I_{Dq} = 2000 \text{ mA}$

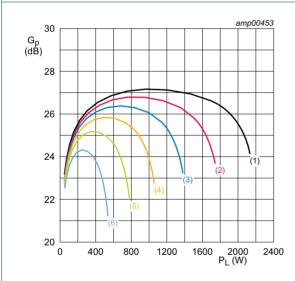
Fig 7. Power gain as a function of output power; typical values



 V_{DS} = 50 V; f = 108 MHz; t_p = 100 μ s; δ = 20 %.

- (1) $I_{Dq} = 50 \text{ mA}$
- (2) $I_{Dq} = 200 \text{ mA}$
- (3) $I_{Dq} = 800 \text{ mA}$
- (4) $I_{Dq} = 2000 \text{ mA}$

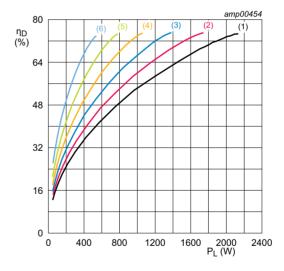
Fig 8. Drain efficiency as a function of output power; typical values



 I_{Dq} = 200 mA; f = 108 MHz; t_p = 100 μ s; δ = 20 %.

- (1) $V_{DS} = 50 \text{ V}$
- (2) $V_{DS} = 45 \text{ V}$
- (3) $V_{DS} = 40 \text{ V}$
- (4) $V_{DS} = 35 \text{ V}$
- (5) $V_{DS} = 30 \text{ V}$
- (6) $V_{DS} = 25 V$

Fig 9. Power gain as a function of output power; typical values



 I_{Dq} = 200 mA; f = 108 MHz; t_p = 100 μ s; δ = 20 %.

- (1) $V_{DS} = 50 \text{ V}$
- (2) $V_{DS} = 45 V$
- (3) $V_{DS} = 40 \text{ V}$
- (4) $V_{DS} = 35 V$
- (5) $V_{DS} = 30 \text{ V}$
- (6) $V_{DS} = 25 V$

Fig 10. Drain efficiency as a function of output power; typical values

8. Package outline

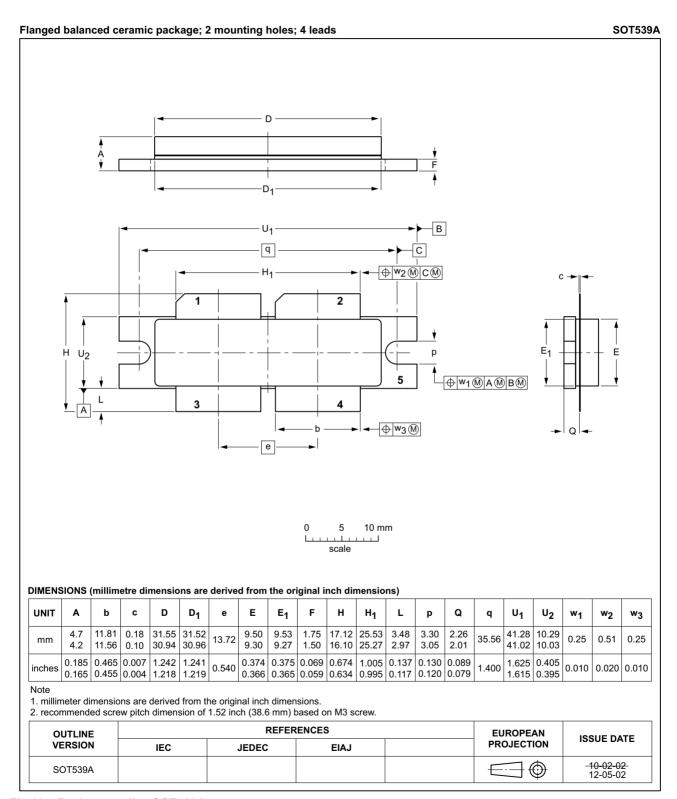


Fig 11. Package outline SOT539A

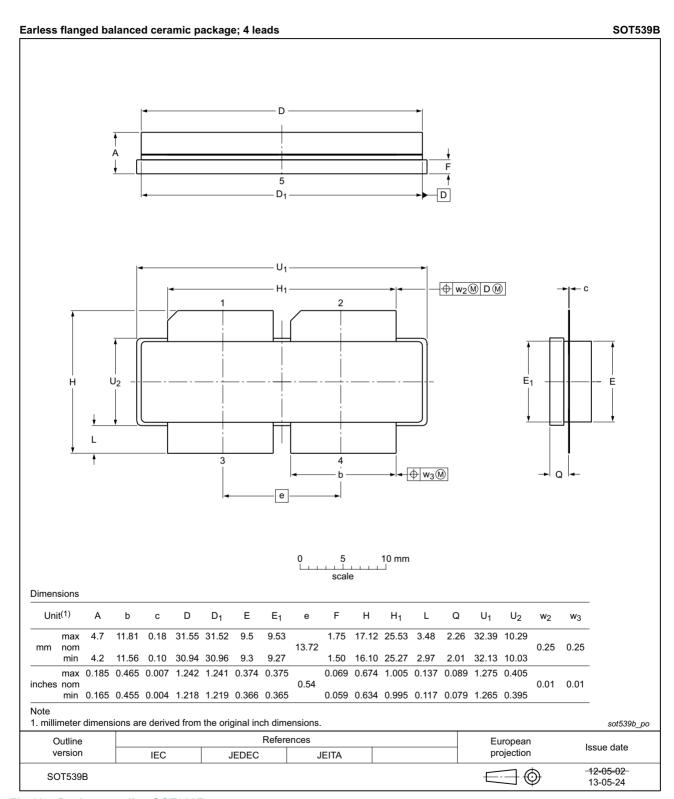


Fig 12. Package outline SOT539B

9. Handling information

CAUTION



This device is sensitive to ElectroStatic Discharge (ESD). Observe precautions for handling electrostatic sensitive devices.

Such precautions are described in the ANSI/ESD S20.20, IEC/ST 61340-5, JESD625-A or equivalent standards.

Table 11. ESD sensitivity

ESD model	Class
Charged Device Model (CDM); According to ANSI/ESDA/JEDEC standard JS-002	C2A [1]
Human Body Model (HBM); According to ANSI/ESDA/JEDEC standard JS-001	2 [2]

- [1] CDM classification C2A is granted to any part that passes after exposure to an ESD pulse of 500 V, but fails after exposure to an ESD pulse of 750 V.
- [2] HBM classification 2 is granted to any part that passes after exposure to an ESD pulse of 2000 V, but fails after exposure to an ESD pulse of 4000 V.

10. Abbreviations

Table 12. Abbreviations

Acronym	Description
CW	Continuous Wave
ESD	ElectroStatic Discharge
HF	High Frequency
LDMOS	Laterally Diffused Metal-Oxide Semiconductor
MTF	Median Time to Failure
SMD	Surface Mounted Device
VSWR	Voltage Standing Wave Ratio

11. Revision history

Table 13. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BLF189XRB_BLF189XRBS v.1	20171003	Product data sheet	-	-

12. Legal information

12.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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- [2] The term 'short data sheet' is explained in section "Definitions"
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